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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : THOMAS HANEDER ET AL.

Filed : Concurrently herewith

Title : FERROELECTRIC TRANSISTOR, USE THEREOF IN A  
MEMORY CELL CONFIGURATION AND METHOD OF  
PRODUCING THE FERROELECTRIC TRANSISTOR

INFORMATION DISCLOSURE STATEMENT

Hon. Commissioner of Patents and Trademarks,  
Washington, D.C. 20231

Sir:

In accordance with 37 C.F.R. 1.98 copies of the following patents and/or publications  
are submitted herewith:

Published European Patent Application No. 0 459 773 A2 (Inoue et al.), dated  
December 4, 1991;

Published European Patent Application No. 0 716 455 A2 (Lee et al.), dated June  
12, 1996;

Published European Patent Application No. 0 716 455 A3 (Lee et al.), dated August  
28, 1996 and

"A Single-Transistor Ferroelectric Memory Cell", Takahashi Nakamura et al., XP  
000557557, IEEE, ISSCC, 1995, Technology Directions, Display, Photonics and  
Ferroelectric Memo, pp. 68-69 and 340.

If no translation of pertinent portions of any foreign language patents or publications mentioned above is included with the aforementioned copies of those applications, patents and/or publications, it is because no existing translation is readily available to the applicant.

Respectfully submitted,



For Applicants

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Date: March 7, 2001

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